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Kind regards,

Team Nexperia



# PSMN085-150K

N-channel TrenchMOS SiliconMAX standard level FET

Rev. 3 — 22 December 2011

Product data sheet

## 1. Product profile

### 1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

### 1.3 Applications

- Computer motherboards
- DC-to-DC convertors
- Switched-mode power supplies

### 1.4 Quick reference data

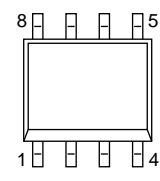
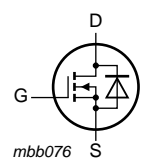
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 150\text{ °C}$	-	-	150	V
$I_D$	drain current	$T_{sp} = 80\text{ °C}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 3</a>	-	-	3.5	A
$P_{tot}$	total power dissipation	$T_{sp} = 80\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	3.5	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 3.5\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	-	67	85	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 4.1\text{ A}$ ; $V_{DS} = 75\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 11</a>	-	12	17	nC



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>SOT96-1 (SO8)</p>	
2	S	source		
3	S	source		
4	G	gate		
5	D	drain		
6	D	drain		
7	D	drain		
8	D	drain		

## 3. Ordering information

Table 3. Ordering information

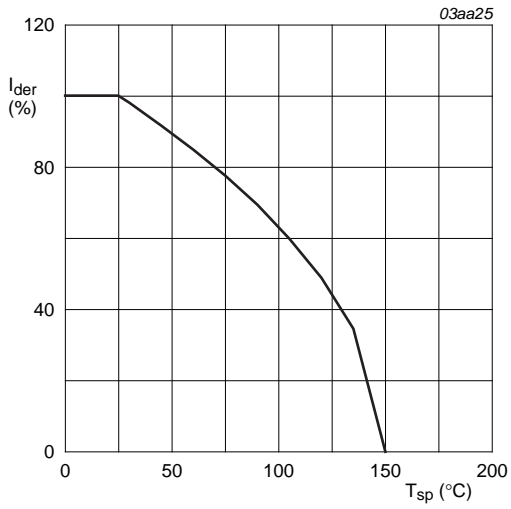
Type number	Package		
	Name	Description	Version
PSMN085-150K	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

## 4. Limiting values

Table 4. Limiting values

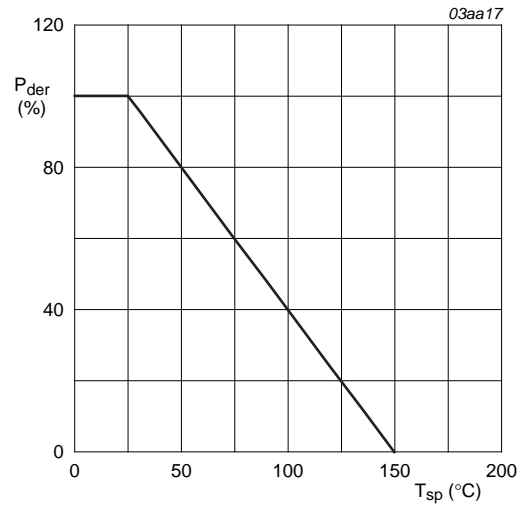
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 150\text{ °C}$	-	150	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$T_{sp} = 80\text{ °C}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 3</a>	-	3.5	A
$I_{DM}$	peak drain current	$T_{sp} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; see <a href="#">Figure 3</a>	-	40	A
$P_{tot}$	total power dissipation	$T_{sp} = 80\text{ °C}$ ; see <a href="#">Figure 2</a>	-	3.5	W
$T_{stg}$	storage temperature		-55	150	°C
$T_j$	junction temperature		-55	150	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{sp} = 80\text{ °C}$	-	3.1	A
$I_{SM}$	peak source current	$T_{sp} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	40	A



$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of solder point temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of solder point temperature

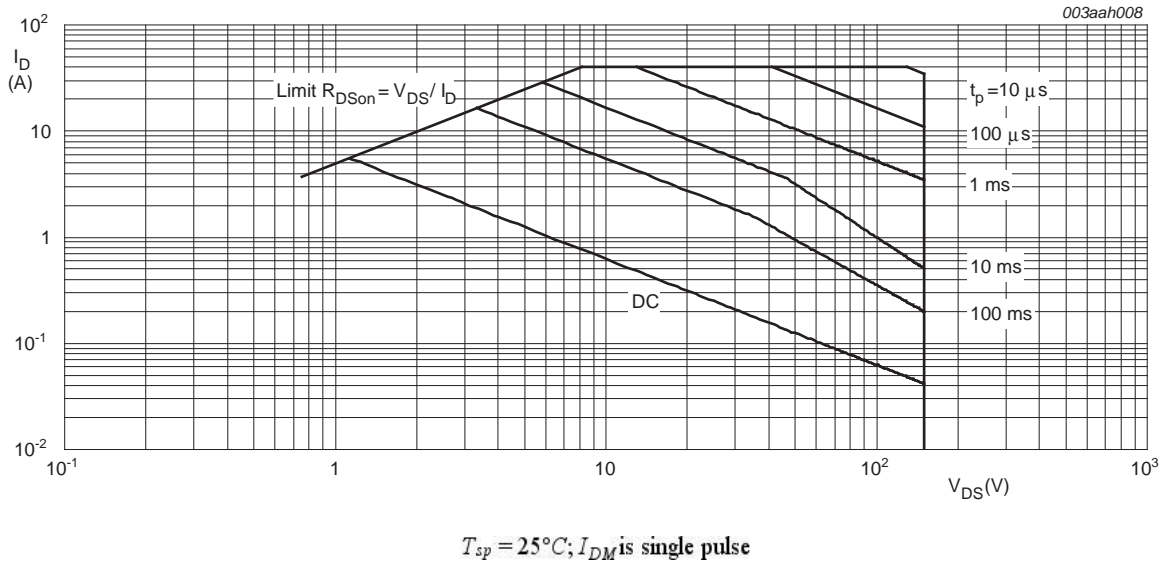


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	mounted on a metal clad substrate ; see <a href="#">Figure 4</a>	-	-	20	K/W

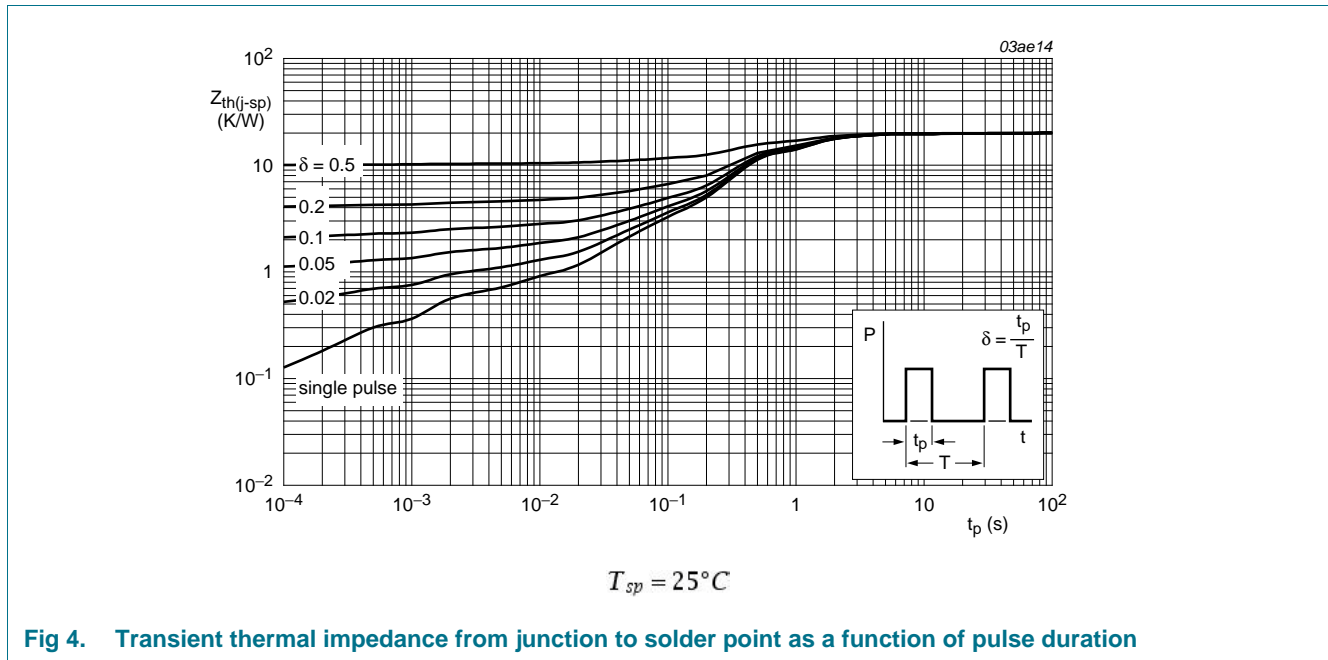
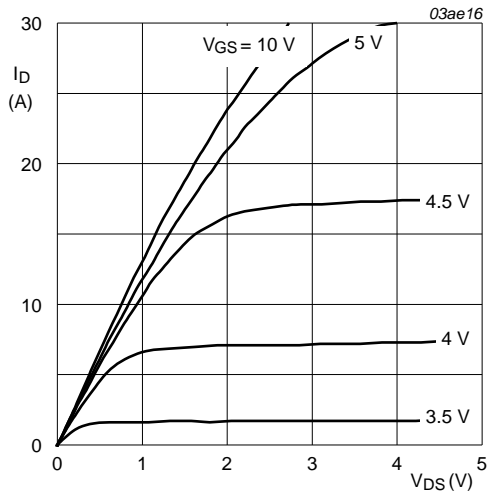


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

## 6. Characteristics

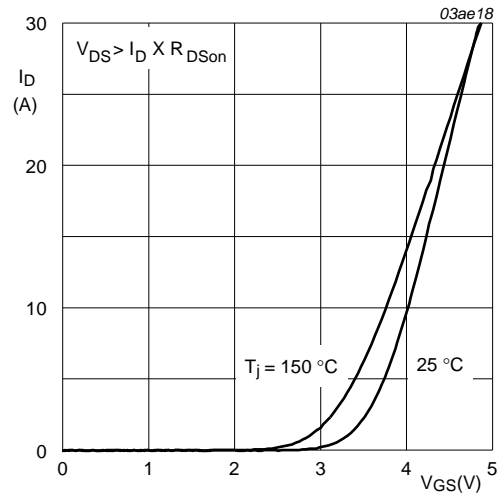
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	150	180	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ }^\circ C$ ; see <a href="#">Figure 8</a>	-	-	6	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 8</a>	2	-	4	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 150 \text{ }^\circ C$ ; see <a href="#">Figure 8</a>	1.2	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 120 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{DS} = 150 V$ ; $V_{GS} = 0 V$ ; $T_j = 150 \text{ }^\circ C$	-	-	0.5	mA
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -20 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V$ ; $I_D = 3.5 A$ ; $T_j = 150 \text{ }^\circ C$ ; see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	-	161	204	m $\Omega$
		$V_{GS} = 10 V$ ; $I_D = 3.5 A$ ; $T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	-	67	85	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 4.1 A$ ; $V_{DS} = 75 V$ ; $V_{GS} = 10 V$ ; $T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 11</a>	-	40	-	nC
$Q_{GS}$	gate-source charge		-	4	-	nC
$Q_{GD}$	gate-drain charge		-	12	17	nC
$C_{iss}$	input capacitance	$V_{DS} = 25 V$ ; $V_{GS} = 0 V$ ; $f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 12</a>	-	1310	-	pF
$C_{oss}$	output capacitance		-	170	-	pF
$C_{rss}$	reverse transfer capacitance		-	80	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 75 V$ ; $R_L = 75 \text{ } \Omega$ ; $V_{GS} = 10 V$ ; $R_{G(ext)} = 6 \text{ } \Omega$ ; $T_j = 25 \text{ }^\circ C$ ; $I_D = 1 A$	-	13	30	ns
$t_r$	rise time		-	17	30	ns
$t_{d(off)}$	turn-off delay time		-	52	80	ns
$t_f$	fall time		-	30	45	ns
$g_{fs}$	transfer conductance	$V_{DS} = 15 V$ ; $I_D = 4.1 A$ ; $T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 14</a>	-	14	-	S
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 2.3 A$ ; $V_{GS} = 0 V$ ; $T_j = 0 \text{ }^\circ C$ ; see <a href="#">Figure 13</a>	-	0.7	1.1	V
$t_{rr}$	reverse recovery time	$I_S = 4.1 A$ ; $di_S/dt = -100 A/\mu s$ ; $V_{GS} = 0 V$ ; $V_{DS} = 25 V$ ; $T_j = 25 \text{ }^\circ C$	-	100	-	ns
$Q_r$	recovered charge		-	0.36	-	$\mu C$



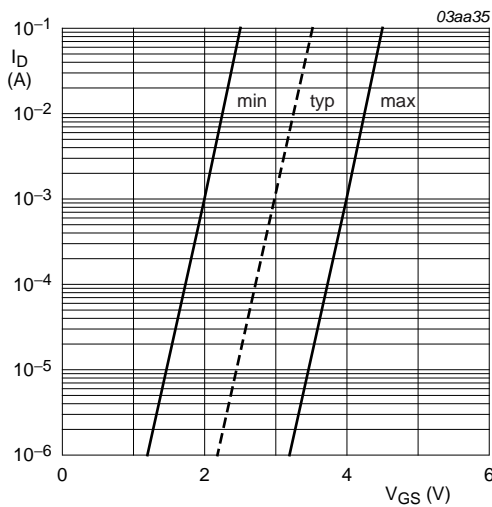
$T_j = 25^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



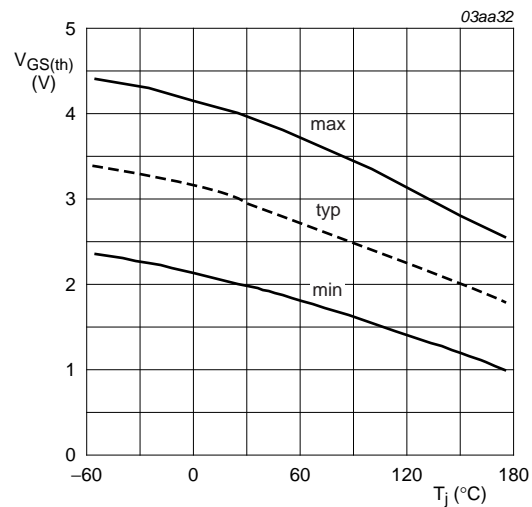
$T_j = 25^\circ\text{C}$  and  $150^\circ\text{C}; V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



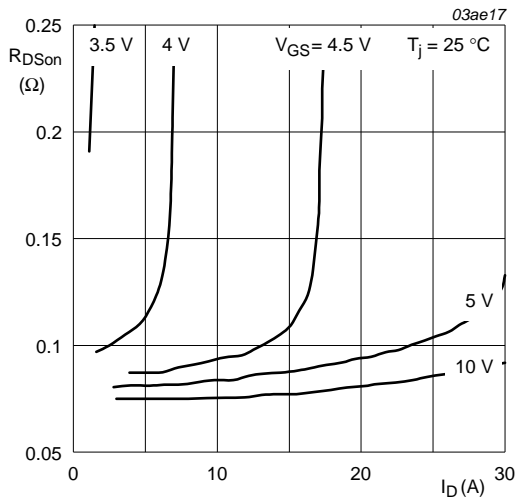
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



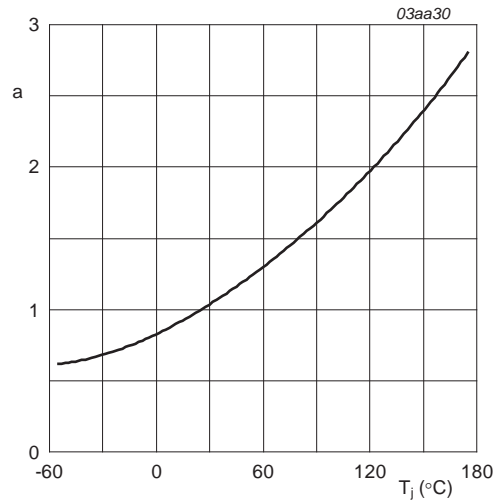
$I_D = 1\text{mA}; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature



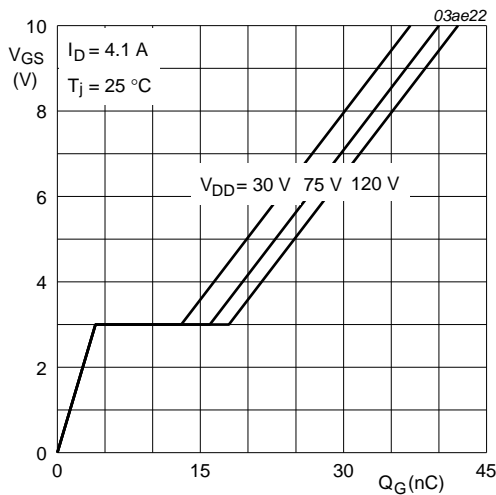
$T_j = 25^\circ\text{C}$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



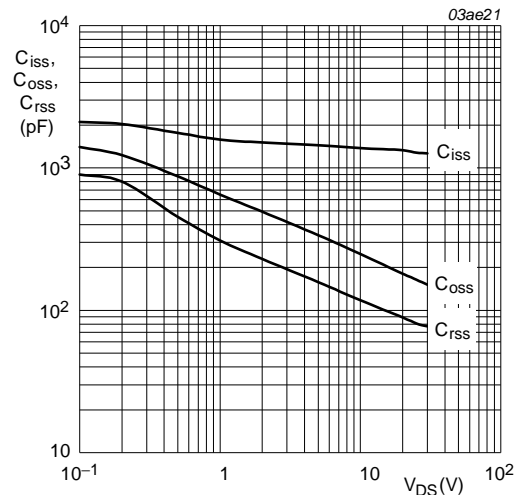
$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



$I_D = 4.1\text{A}; V_{DS} = 30\text{V}, 75\text{V}$  and  $120\text{V}$

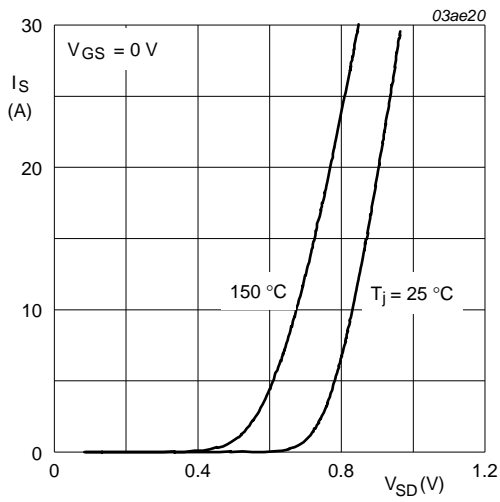
Fig 11. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{V}; f = 1\text{MHz}$

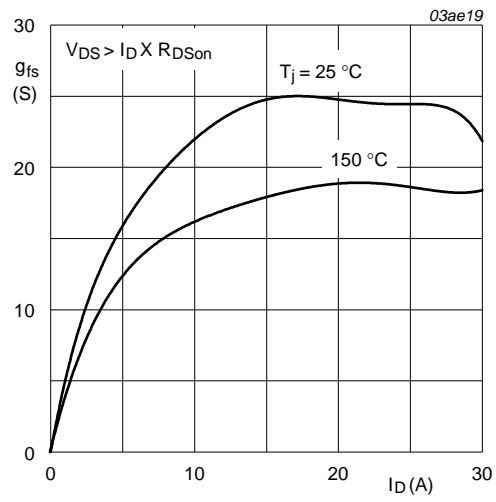
Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values





$T_j = 25^\circ\text{C}$  and  $150^\circ\text{C}; V_{GS} = 0\text{V}$

Fig 13. Source current as a function of source-drain voltage; typical values



$T_j = 25^\circ\text{C}$  and  $150^\circ\text{C}; V_{DS} > I_D \times R_{DSon}$

Fig 14. Forward transconductance as a function of drain current; typical values

7. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1

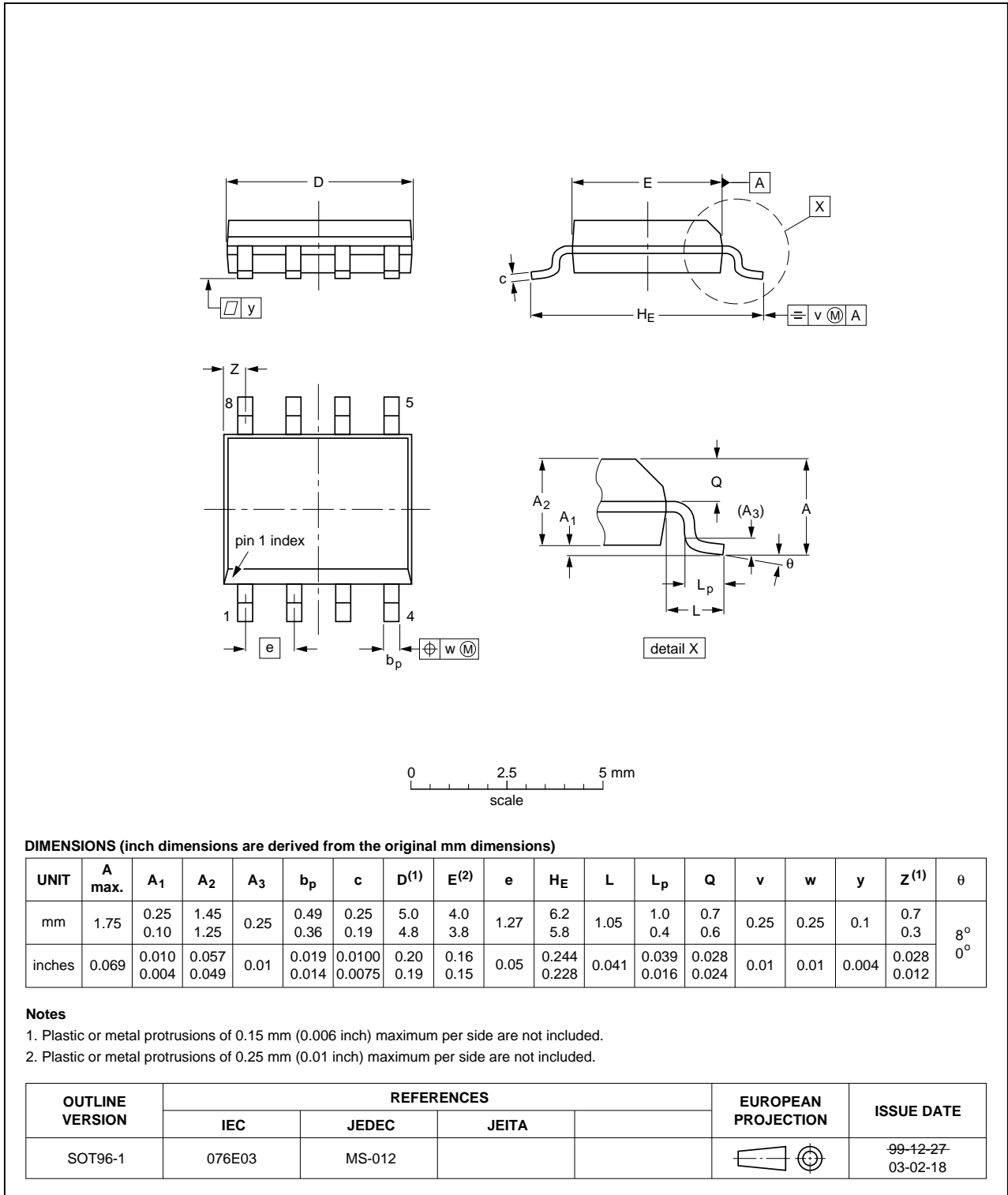


Fig 15. Package outline SOT96-1 (SO8)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN085-150K v.3	20111222	Product data sheet	-	PSMN085_150K v.2
Modifications:	• Various changes to content.			
PSMN085_150K v.2	20100301	Product data sheet	-	PSMN085_150K v.1

## 9. Legal information

### 9.1 Data sheet status

Document status <a href="#">[1]</a> <a href="#">[2]</a>	Product status <a href="#">[3]</a>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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